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PCN# :P222A
Issue Date : Feb. 21, 2012

DESIGN/PROCESS CHANGE NOTIFICATION

This is to inform you that a change is being made to the following products.

This is a minor change that has no impact on product quality, reliability, electrical or mechanical performance. Affected products will remain fully compliant to all published specifications. Notification is being made for informational purposes only and there is no approval required. Products incorporating this change may be shipped interchangeably with existing unchanged products.

Please contact your local Customer Quality Engineer if you have any questions regarding this notification. Alternatively, you may send an email request for information to PCNSupport@fairchildsemi.com.

Implementation of change:

Expected First Shipment Date for Changed Product :Jun. 30, 2012

Expected First Date Code of Changed Product :1227

Last Date for Shipment of Unchanged Product :Jun. 30, 2012

Description of Change (From) :
The FAB3102 is manufactured on TSMC 0.18um BCD process. Two high voltage mask layers DPW(deep P-well) and HVPB(p-body for NLDMOS) will be removed from current fab process.

Description of Change (To) :
The FAB3102 is manufactured on TSMC 0.18um BCD process will not have the two high voltage mask layers DPW(deep P-well) and HVPB(p-body for NLDMOS) in the process.

Reason for Change:
The FAB3102 does not utilize the high voltage capability. These two high voltage mask layers DPW(deep P-well) and HVPB(p-body for NLDMOS) have no shapes in the layout and no implants from these process steps.

Affected Product(s):

FAB3102UCX		